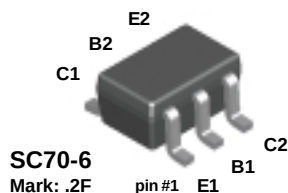


FFB2907A

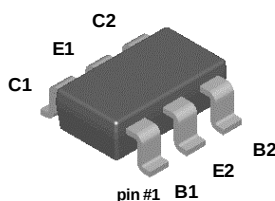


SC70-6

Mark: .2F

NOTE: The pinouts are symmetrical; pin 1 and pin 4 are interchangeable. Units inside the carrier can be of either orientation and will not affect the functionality of the device.

FMB2907A

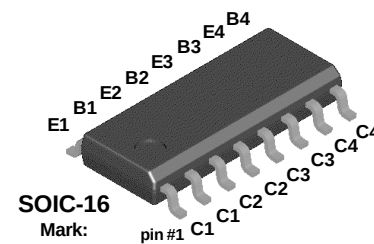


SuperSOT™-6

Mark: .2F

Dot denotes pin #1

MMPQ2907A



SOIC-16

Mark:
MMPQ2907A

PNP Multi-Chip General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 63.

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	60	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	600	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Characteristic	Max			Units
		FFB2907A	FMB2907A	MMPQ2907A	
P_D	Total Device Dissipation	300	700	1,000	mW
	Derate above 25°C	2.4	5.6	8.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	415	180		$^\circ\text{C/W}$
				125	$^\circ\text{C/W}$
				240	$^\circ\text{C/W}$

PNP Multi-Chip General Purpose Amplifier

(continued)

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10\text{ mA}$, $I_B = 0$	60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$	60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$	5.0			V
I_B	Base Cutoff Current	$V_{CB} = 30\text{ V}$, $V_{EB} = 0.5\text{ V}$			50	nA
I_{CEX}	Collector Cutoff Current	$V_{CE} = 30\text{ V}$, $V_{BE} = 0.5\text{ V}$			50	nA
I_{CBO}	Collector Cutoff Current	$V_{CB} = 50\text{ V}$, $I_E = 0$ $V_{CB} = 50\text{ V}$, $I_E = 0$, $T_A = 125^\circ\text{C}$			0.02 20	μA μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 0.1\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}$, $V_{CE} = 10\text{ V}^*$ $I_C = 500\text{ mA}$, $V_{CE} = 10\text{ V}^*$	75 100 100 100 50		300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$ $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$			0.4 1.6	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150\text{ mA}$, $I_B = 15\text{ mA}^*$ $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$			1.3 2.6	V V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 50\text{ mA}$, $V_{CE} = 20\text{ V}$, $f = 100\text{ MHz}$		250		MHz
C_{obo}	Output Capacitance	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 100\text{ kHz}$		6.0		pF
C_{ibo}	Input Capacitance	$V_{EB} = 2.0\text{ V}$, $I_C = 0$, $f = 100\text{ kHz}$		12		pF

SWITCHING CHARACTERISTICS

t_{on}	Turn-on Time	$V_{CC} = 30\text{ V}$, $I_C = 150\text{ mA}$, $I_{B1} = 15\text{ mA}$		30		ns
t_d	Delay Time			8.0		ns
t_r	Rise Time			20		ns
t_{off}	Turn-off Time	$V_{CC} = 6.0\text{ V}$, $I_C = 150\text{ mA}$ $I_{B1} = I_{B2} = 15\text{ mA}$		80		ns
t_s	Storage Time			60		ns
t_f	Fall Time			20		ns

*Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Spice Model

PNP (Is=650.6E-18 Xti=3 Eg=1.11 Vaf=115.7 Bf=231.7 Ne=1.829 Ise=54.81f Ikf=1.079 Xtb=1.5 Br=3.563 Nc=2 Isc=0 Ikr=0 Rc=.715 Cjc=14.76p Mjc=.5383 Vjc=.75 Fc=.5 Cje=19.82p Mje=.3357 Vje=.75 Tr=111.3n Tf=603.7p Itf=.65 Vtf=5 Xtf=1.7 Rb=10)

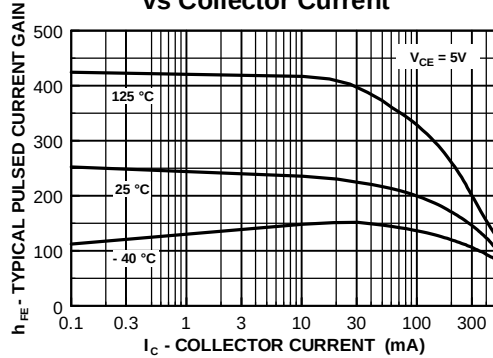
FFB2907A / FMB2907A / MMPQ2907A

PNP Multi-Chip General Purpose Amplifier

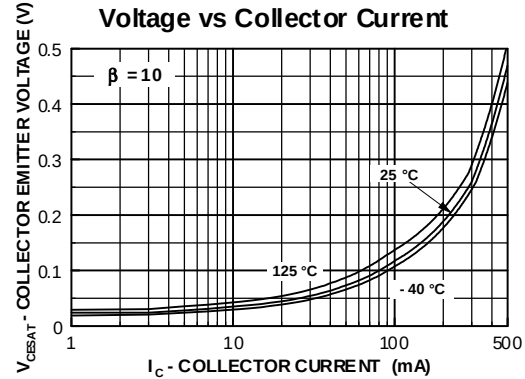
(continued)

Typical Characteristics

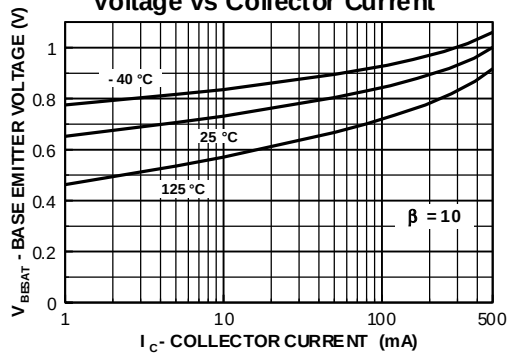
Typical Pulsed Current Gain
vs Collector Current



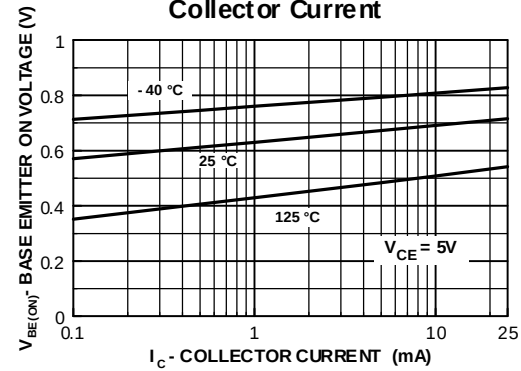
Collector-Emitter Saturation
Voltage vs Collector Current



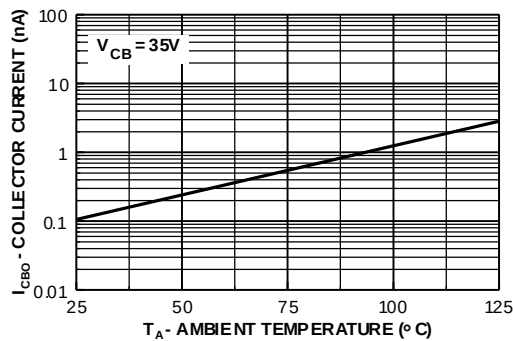
Base-Emitter Saturation
Voltage vs Collector Current



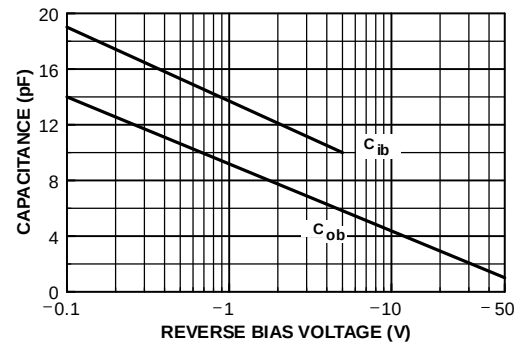
Base Emitter ON Voltage vs
Collector Current



Collector-Cutoff Current
vs Ambient Temperature



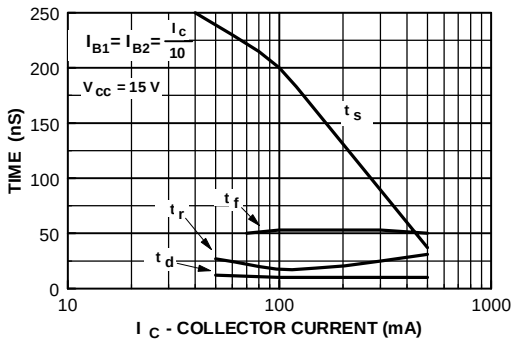
Input and Output Capacitance
vs Reverse Bias Voltage



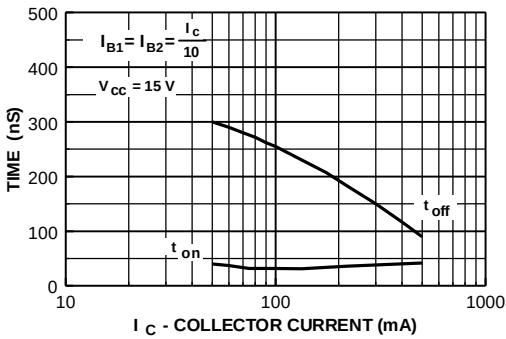
FFB2907A / FMB2907A / MMPQ2907A

Typical Characteristics (continued)

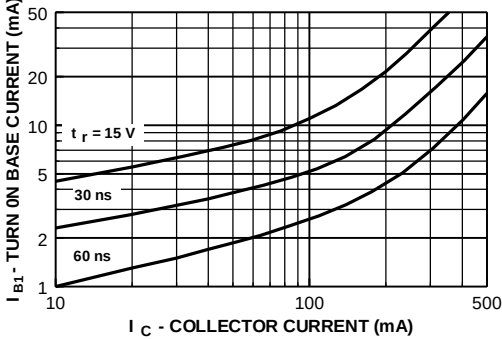
Switching Times
vs Collector Current



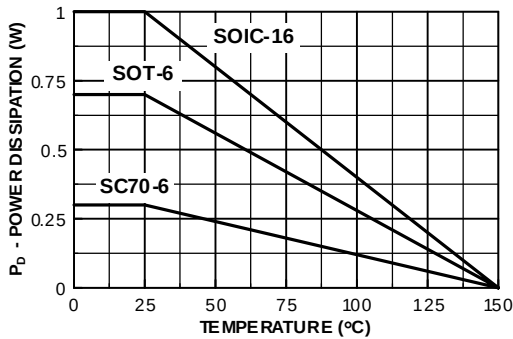
Turn On and Turn Off Times
vs Collector Current



Rise Time vs Collector
and Turn On Base Currents

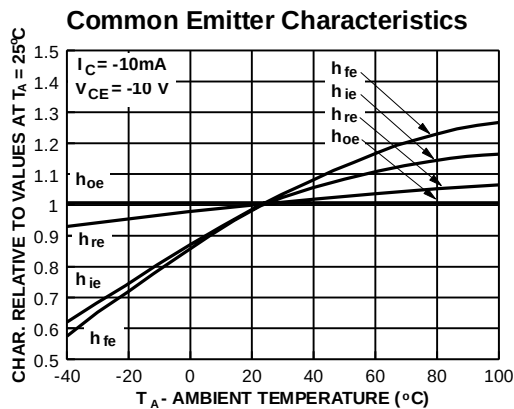
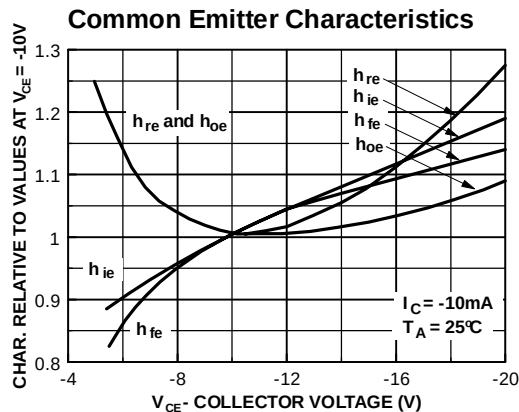
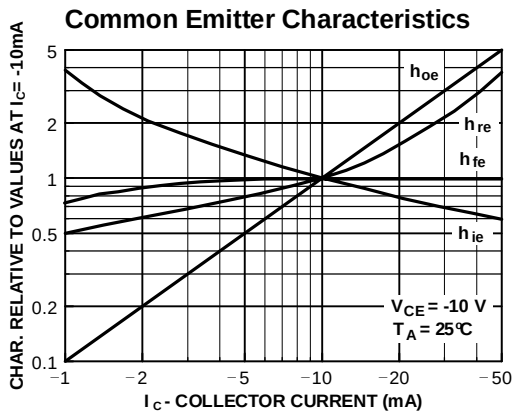


Power Dissipation vs
Ambient Temperature



PNP Multi-Chip General Purpose Amplifier
(continued)

Typical Common Emitter Characteristics (f = 1.0kHz)



FFB2907A / FMB2907A / MMPQ2907A

Test Circuits

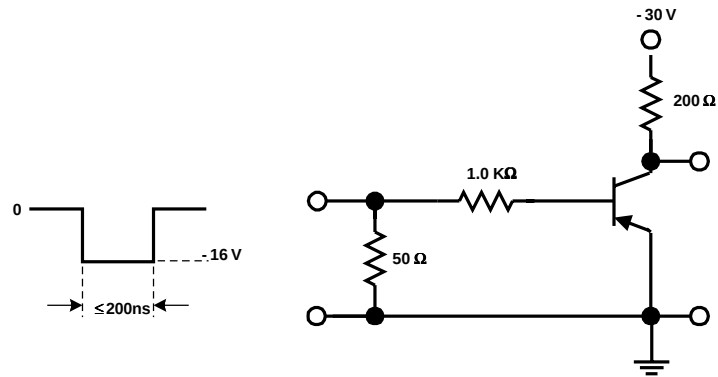


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

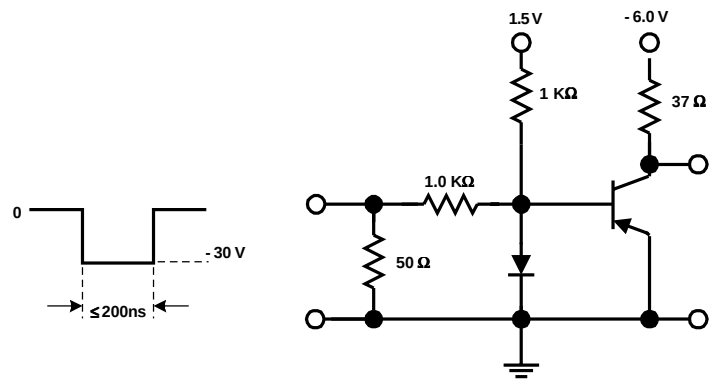


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

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